

1. Assume a baseband analog circuit with bandwidth limited by load capacitance (CL). To double the SNR, the designer doubled CL but kept the bias point (V^*) of the transistors unchanged. He modified the bias currents to keep the bandwidth constant. The area of the circuit will be roughly multiplied by ____.

$$\propto \text{SNR} = \frac{2V_p^2 V_{R_D}^2 C_L}{(V^*)^2 kT (1 + \gamma g_m R_D)} \rightarrow \text{SNR} \times 2$$

\downarrow
Const

$$\propto \text{GBW} = \frac{g_m}{2\pi C_L} \rightarrow g_m \times 2 \rightarrow \frac{g_m}{I_D} = \text{Const} \rightarrow I_D \times 2 \rightarrow W \times 2$$

$$\propto \text{Area} \times 2$$

2. Assume a baseband analog circuit with bandwidth limited by load capacitance (CL). To add one bit of resolution, the designer quadrupled CL. To keep the bandwidth constant, he halved V^* wherever needed, and the power consumption should be multiplied by ____.

$$\propto \text{SNR} = \frac{2V_p^2 V_{R_D}^2 C_L}{(V^*)^2 kT (1 + \gamma g_m R_D)} \rightarrow \text{SNR} \times 4$$

$$\propto \text{GBW} = \frac{g_m}{2\pi C_L} \rightarrow g_m \times 4$$

$$\propto V^* \times \frac{1}{2} \rightarrow \frac{g_m}{I_D} \times 2 \rightarrow g_m \times 4 \rightarrow I_D \times 2 \rightarrow P_{\text{bias}} \times 2$$

3. In an RF system with a specific bandwidth dictated by a standard, the total integrated noise is determined by the ____.

By thermal noise (resistors)

4. A low-noise amplifier has low output-referred noise.

False \rightarrow low input referred noise

5. In an analog baseband system, the total integrated noise is determined by the ____.

By Capacitance $\frac{kT}{C}$

6. Assume a baseband analog circuit with bandwidth limited by MOSFET capacitance. The designer doubled the bias currents but kept the bias point (g_m/I_D) of the transistors unchanged. Then ____.

$$\propto \frac{g_m}{I_D} = \text{Const} \rightarrow g_m \times 2 \rightarrow I_D \times 2 \rightarrow W \times 2 \rightarrow C \times 2$$

$$\propto \text{GBW} = \frac{g_m}{C} \times 2 = \text{Const}$$

$$\propto V_n^2(f) = \frac{4kT\gamma}{g_m} \rightarrow V_n^2(f) \times \frac{1}{2}$$

\propto speed Const, Noise decrease

7. Achieving high SNR is more difficult in deep sub-micron technologies because ____.

V_{DD} decrease and $\text{SNR} \propto V_{DD}^2$

8. For a wideband MOSFET amplifier, the most important noise contribution is due to ____.

thermal noise

9. In a baseband analog circuit, if the bandwidth of your circuit is 10s of MHz, then you don't have to worry about Flicker noise.

False

10. The flicker noise of a MOSFET will decrease if ____.

bias current is increased at a constant bias point (g_m/I_D) $g_m/I_D = \text{Const} \rightarrow \frac{I_D}{W} = \text{Const} \rightarrow I_D \uparrow, W \uparrow, \text{Area} \uparrow, \text{noise} \downarrow$ ✓

temperature is decreased $V_{n, \text{flicker}} \propto \sqrt{f(T)}$ ✗

g_m/I_D is increased at a constant bias current $g_m/I_D \uparrow, I_D \downarrow, I_D \text{ Const}, W \uparrow, \text{Area} \uparrow, \text{noise} \downarrow$ ✓

channel length is increased at a constant bias current and g_m/I_D $g_m/I_D = \text{Const}, I_D \text{ Const}, \frac{W}{L} = \text{Const} \rightarrow L \uparrow, W \uparrow, \text{Area} \uparrow, \text{noise} \downarrow$ ✓